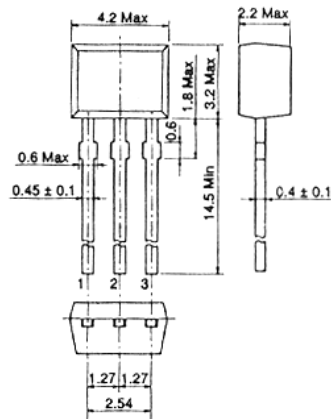


## 2SA1390

SILICON PNP EPITAXIAL  
LOW FREQUENCY AMPLIFIER



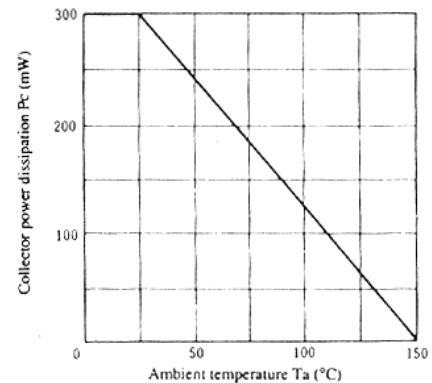
(SPAK)

1. Emitter
  2. Collector
  3. Base
- (Dimensions in mm)

### ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1121	Unit
Collector to base voltage	V <sub>CB0</sub>	-35	V
Collector to emitter voltage	V <sub>CEO</sub>	-35	V
Emitter to base voltage	V <sub>EBO</sub>	-4	V
Collector current	I <sub>C</sub>	-500	mA
Collector power dissipation	P <sub>C</sub>	300	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### MAXIMUM COLLECTOR DISSIPATION CURVE



### ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0	-35	—	—	V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -1mA, R <sub>BE</sub> = ∞	-35	—	—	V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0	-4	—	—	V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = -20V, I <sub>E</sub> = 0	—	—	-0.5	μA
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA**	—	-0.2	-0.6	V
DC current transfer ratio	h <sub>FE1</sub>	V <sub>CE</sub> = -3V, I <sub>C</sub> = -10mA	60	—	320	
DC current transfer ratio	h <sub>FE2</sub>	V <sub>CE</sub> = -3V, I <sub>C</sub> = -500mA**	10	—	—	
Base to emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -3V, I <sub>C</sub> = -10mA	—	-0.64	—	V

\* The 2SA1390 is grouped by h<sub>FE1</sub> as follows.

\*\* Pulse Test

B	C	D
60 to 120	100 to 200	160 to 320

■ See characteristic curves of 2SA673.